

TAIYANGNEWS

ALL ABOUT SOLAR POWER

Solar Technology Conference India 2026

📅 Feb 5-6, 2026 ⌚ 09:30 AM

📍 Hotel Pride Plaza - Aerocity, New Delhi, India

Leadmicro 微导

股票代码 688147

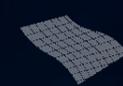
TOPCon 4.0, EPD Loss Analysis, Edge Passivation Mechanisms and Equipment Solutions

Baochen LIAO (CTO/Professor)

2026.02.06

江苏微导纳米科技股份有限公司

Jiangsu Leadmicro Nano-Technology Co., Ltd.



目录

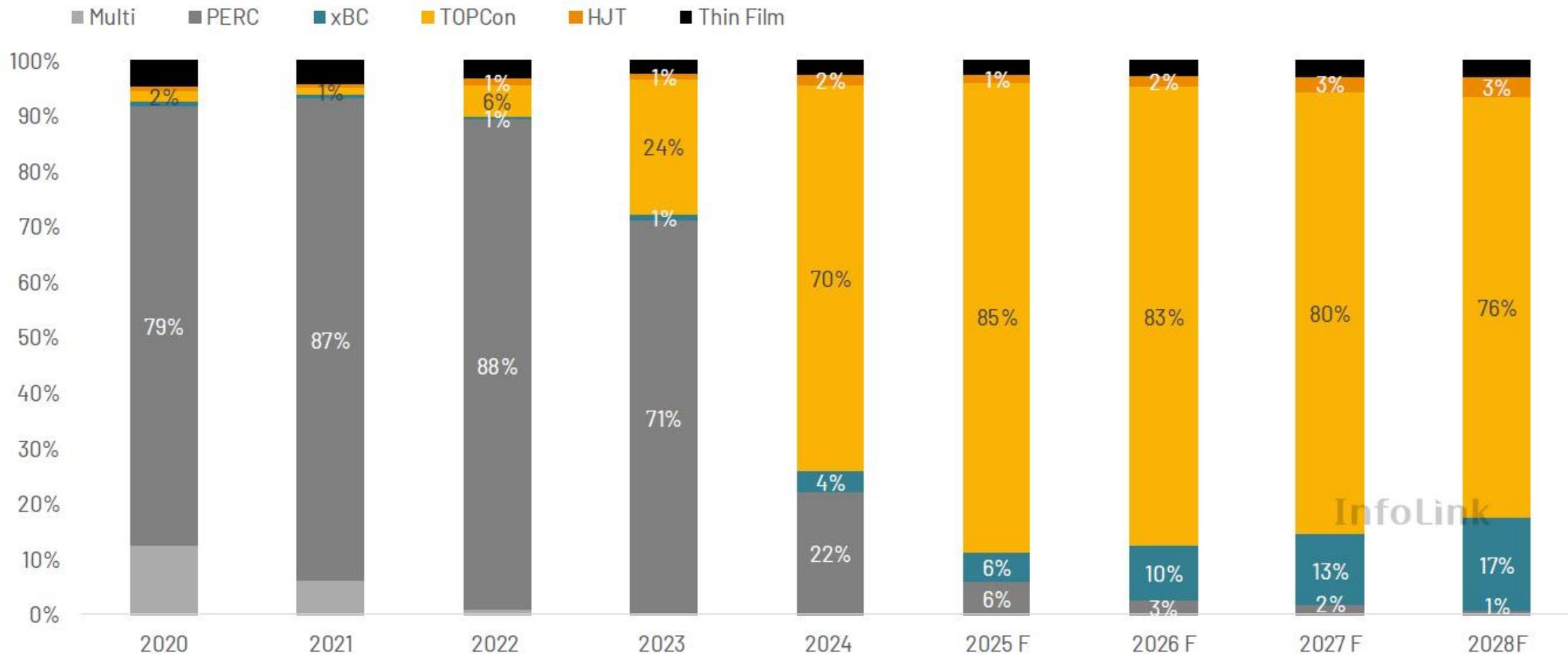
CONTENTS

- Recent Progress of Cell Technologies
- TOPCon 4.0 Solutions
- EPD Loss Analysis
- EPD Equipment Solutions
- EPD Future Outlook
- Company Introduction
- Conclusion

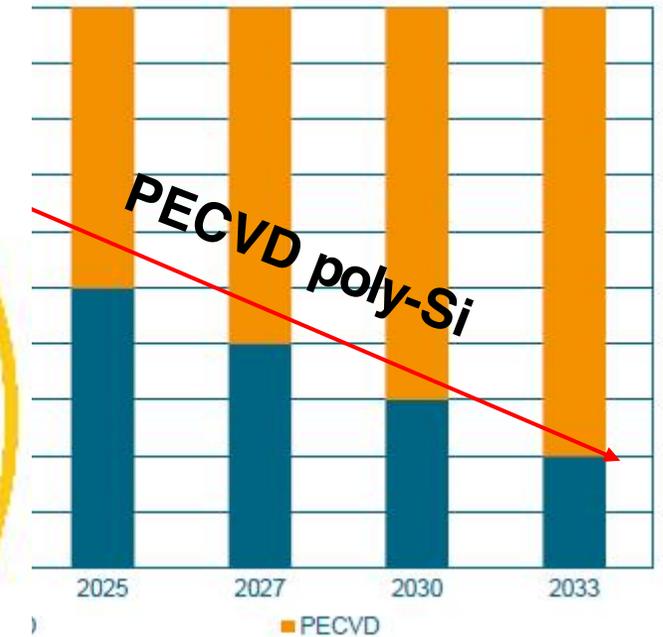
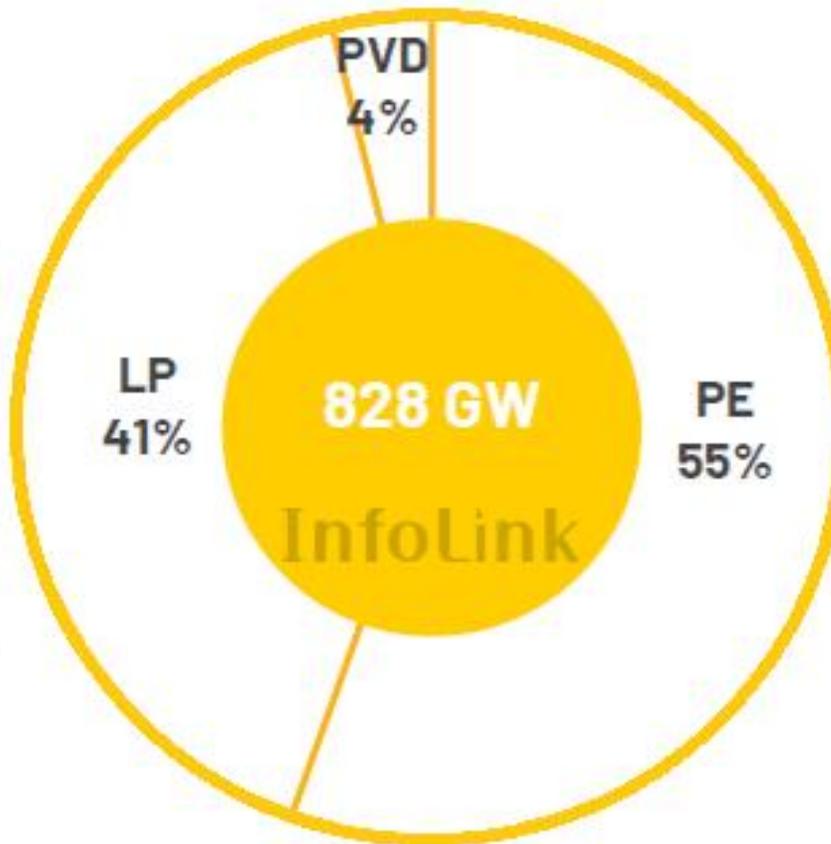
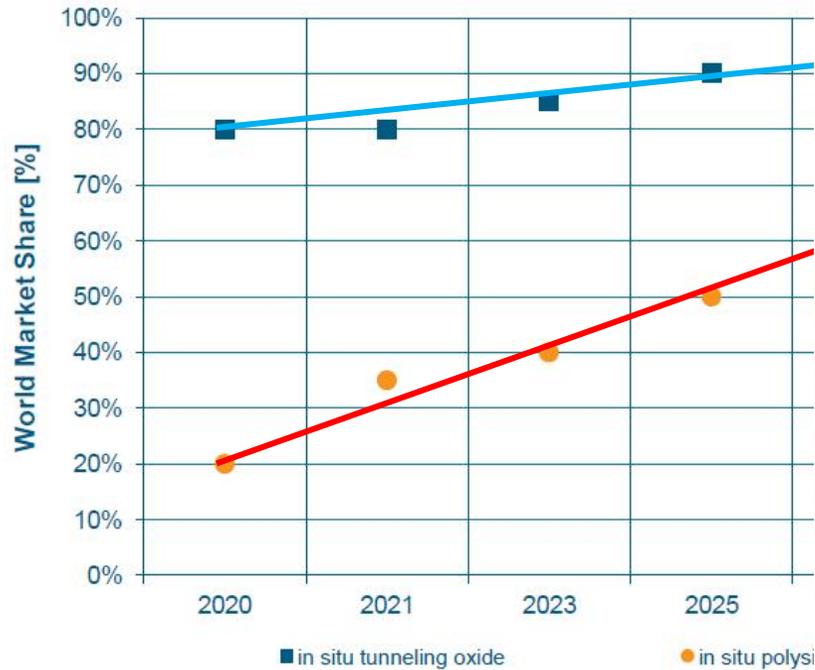
01

Recent Progress of Cell Technologies

➤ Trend of Cell Technology



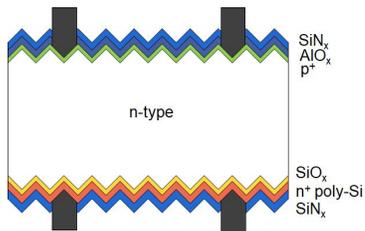
- Tunnel oxide and poly-Si: in-situ
- Poly-Si : LPCVD VS PECVD (~ 80%)



24%

PE-TOPCon 0.0
(Pilot-line)

1. Completed **feasibility pilot-line study**
2. Solved **process & equip. bottlenecks**
3. Eta > 24%

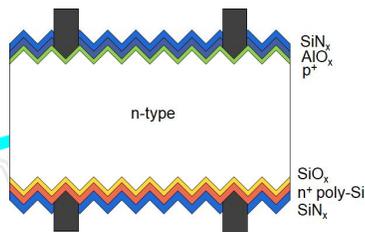


2021.06

26%

PE-TOPCon 1.0
(GW Scale mass-prod. evalu.)

1. Completed **1GW Mass-prod. study**
2. Solved **Yield bottleneck**
3. Eta > 26%, Yield > 97%

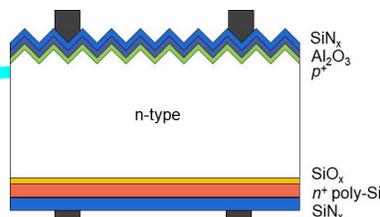


2022.06

26.6%

PE-TOPCon 1.6
(Factory level Mass-prod.)

1. **Factory level expansion**
2. Solved mass-prod. expansion problems.
3. Eta: **rear morphology, anneal opt., screen-printing etc.**

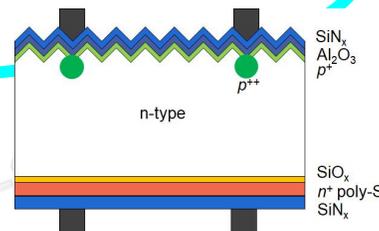


2023.06

26%

PE-TOPCon 2.0
(Mass-prod.)

1. Cost: **2% PH3 → 8% PH3 (~3 times↓)**
2. Eta : **SE, rear opt. polish+paste, Tox+Poly etc.**

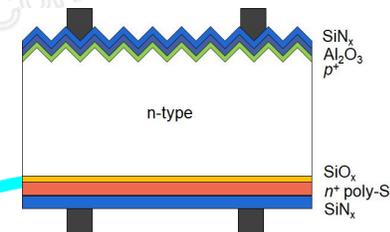


2023.12

> 26%

PE-TOPCon 3.0
(Mass-prod.)

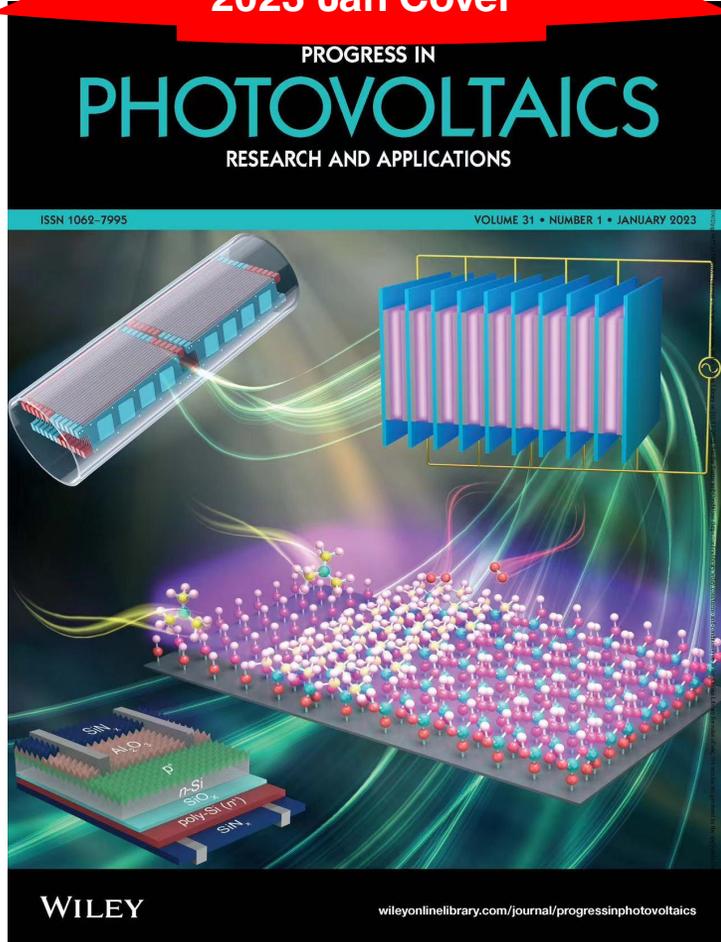
1. **Laser assisted firing**
2. **Front-side opt.**



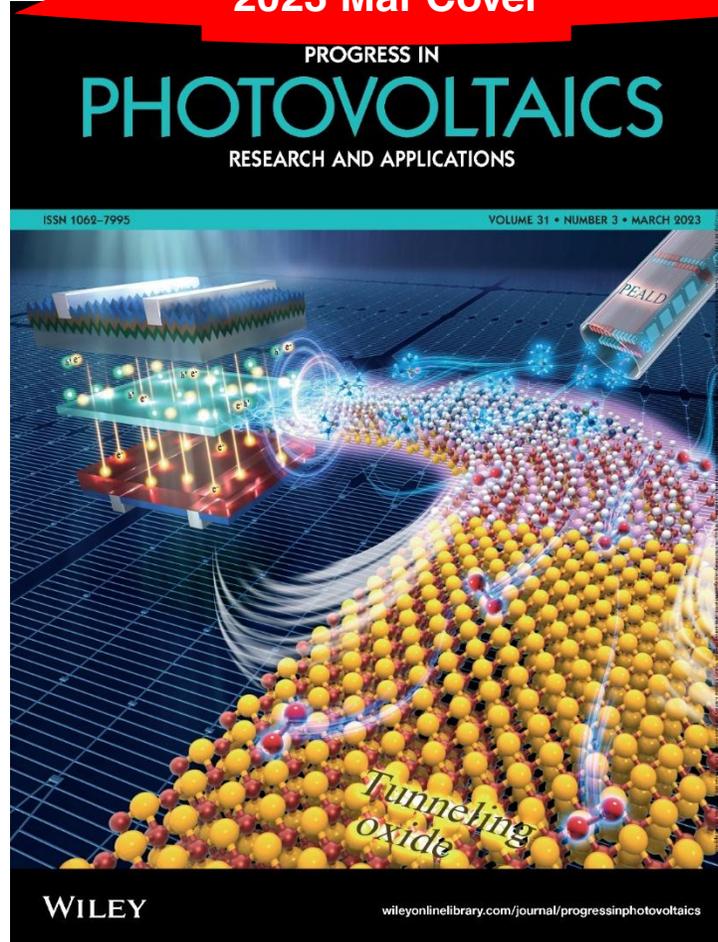
2024.12

- **Selected as PIP featured cover twice**
- **Well recognized internationally (including Europe, US, Lartin, Spain, India etc.)**

2023 Jan Cover



2023 Mar Cover



pv magazine

SOLAR NEWS

TOPCon solar cell achieves 24.2% efficiency via plasma-assisted atomic layer deposition tech

TOPCON SOLAR CELL ACHIEVES 24.2% EFFICIENCY VIA NEW PLASMA-ASSISTED ATOMIC LAYER DEPOSITION TECH

In Solar News, Sustainability by EISol / 17 October 2022 / Leave a Comment

An international research team has fabricated a tunnel oxide passivated contacts (TOPCon) solar cell through a new technique enabling the control of tunnel oxide deposition at the atomic scale. The scientists described the proposed method as an innovative tube-type industrial plasma-assisted atomic layer deposition (PEALD) technique. They claimed that it can produce high-quality dense tunnel silicon oxide (SiO_x) films at

A team of researchers from the Chinese Academy of Sciences (CAS) has developed a new technology for depositing atomic layer deposition (ALD) on TOPCon solar cells, achieving a record efficiency of 24.2%.

La cellule solaire TOPCon atteint une efficacité de 24,2 % grâce à la nouvelle technologie de dépôt de couche atomique assistée par plasma

Les scientifiques ont décrit la méthode proposée comme une nouvelle technique de dépôt de couche atomique industrielle assistée par plasma (PEALD) de type tunnel. Selon eux, il peut produire des films d'oxyde de haute qualité, à faible coût et à haut rendement.

Selon les chercheurs, cette méthode de dépôt chimique en phase vapeur permet la fabrication de modules solaires

MERCOM
clean energy insights

TOPCon Solar Cells Achieve 22.8% Efficiency With Plasma-Aided Atomic Layer Deposition

The tunnel oxide deposition thickness was controlled at the atomic scale for higher efficiency

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ALL ABOUT SOLAR POWER

Interview – Baochen LIAO, Leadmicro

Single sided process with PECVD is the key enabler for TOPCon

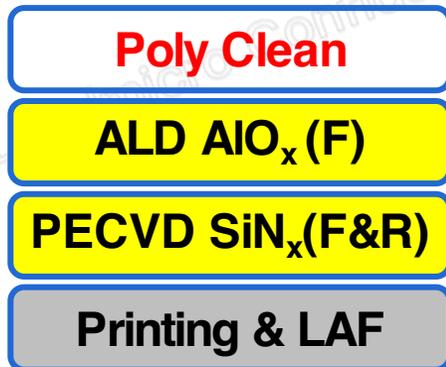
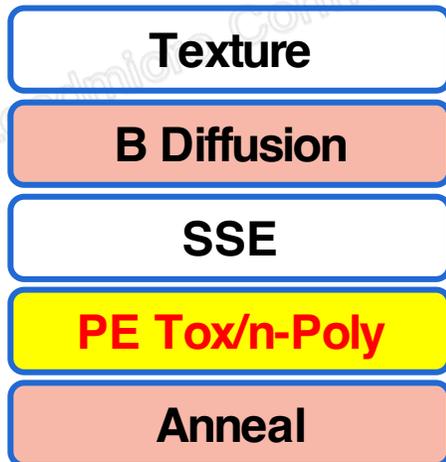
the method wherein they deposit an ultrathin silicon oxide layer of 1-2 nm on the Si (n+) interface. The tunnel oxide thickness was controlled at the atomic scale for

Proprietary

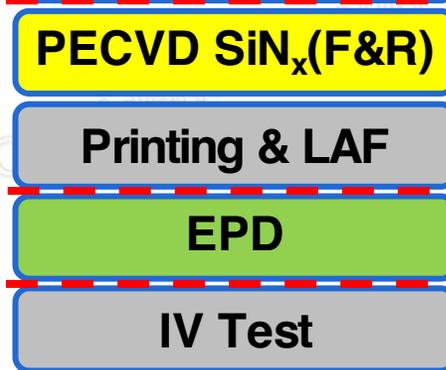
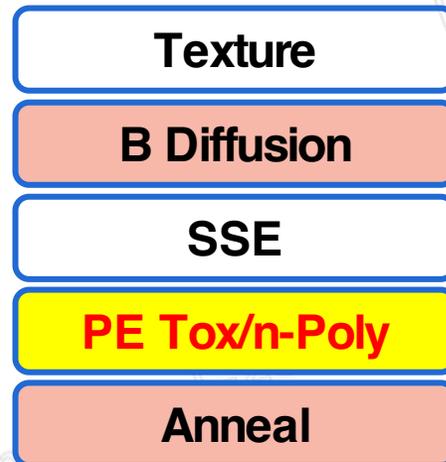
02

TOPCon 4.0 Solutions

PE-TOPCon 3.0



PE-TOPCon 4.0



New

Single to Double side

New

TOP Performance

World Leading
1.5Xboat New Tech

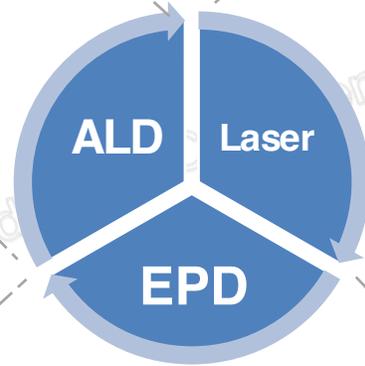
TOP Performance
Highest Throughput



**World Leading
1.5Xboat New Tech**



TOP Performance



**TOP Performance
Highest Throughput**



2.1

Rear Poly Finger by Laser



Laser Cutting for EPD



Laser Assisted Firing



Poly Thinning

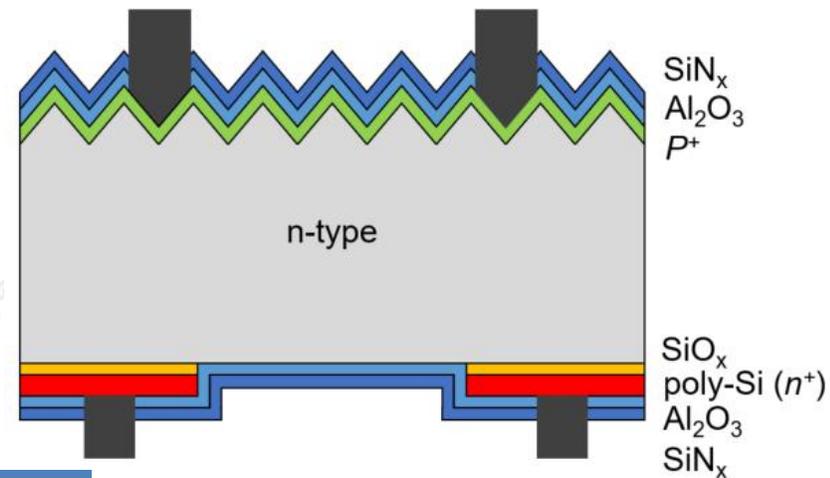


TBC Patterning

Capacity High

210R: 6300-7000 pcs/h

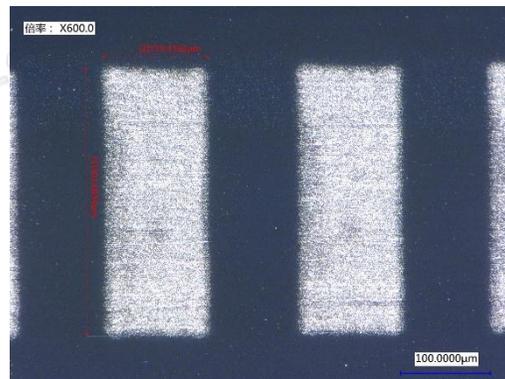
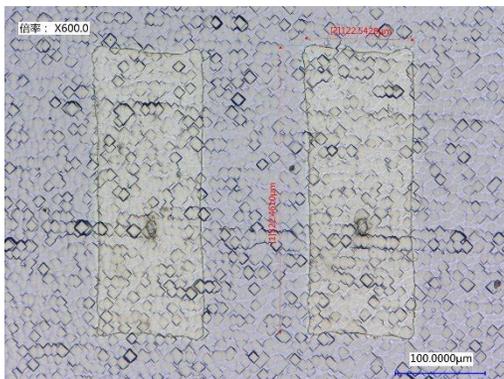
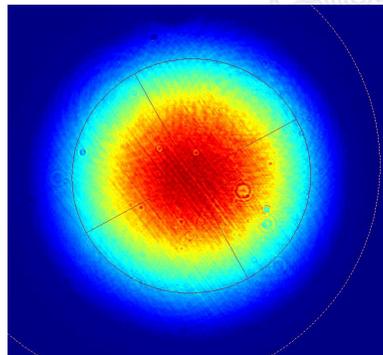
Stability High



	Eta.
with rear poly finger	0.16% ↑

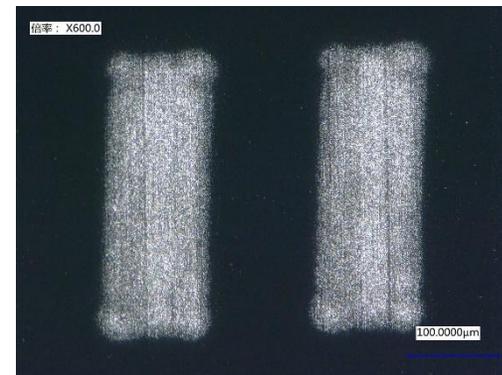
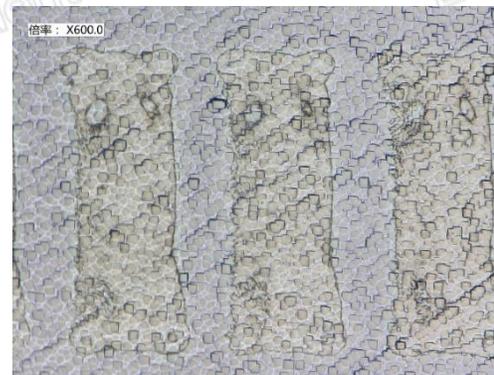
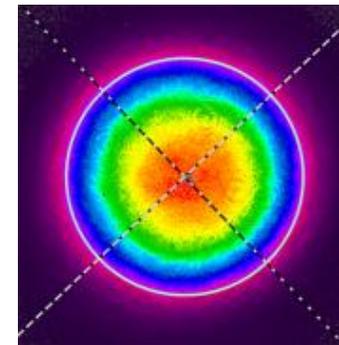
LM Laser:
~110W

~110M



Others:
~100W

~100M



- Laser output power
- Laser spot roundness
- Shaping uniformity

2.2 ALD

PE-TOPCon 4.0

Texture

B Diffusion

SSE

PE Tox/n-Poly

Anneal

Poly-Finger (R)

Poly Clean

ALD AlO_x (F)

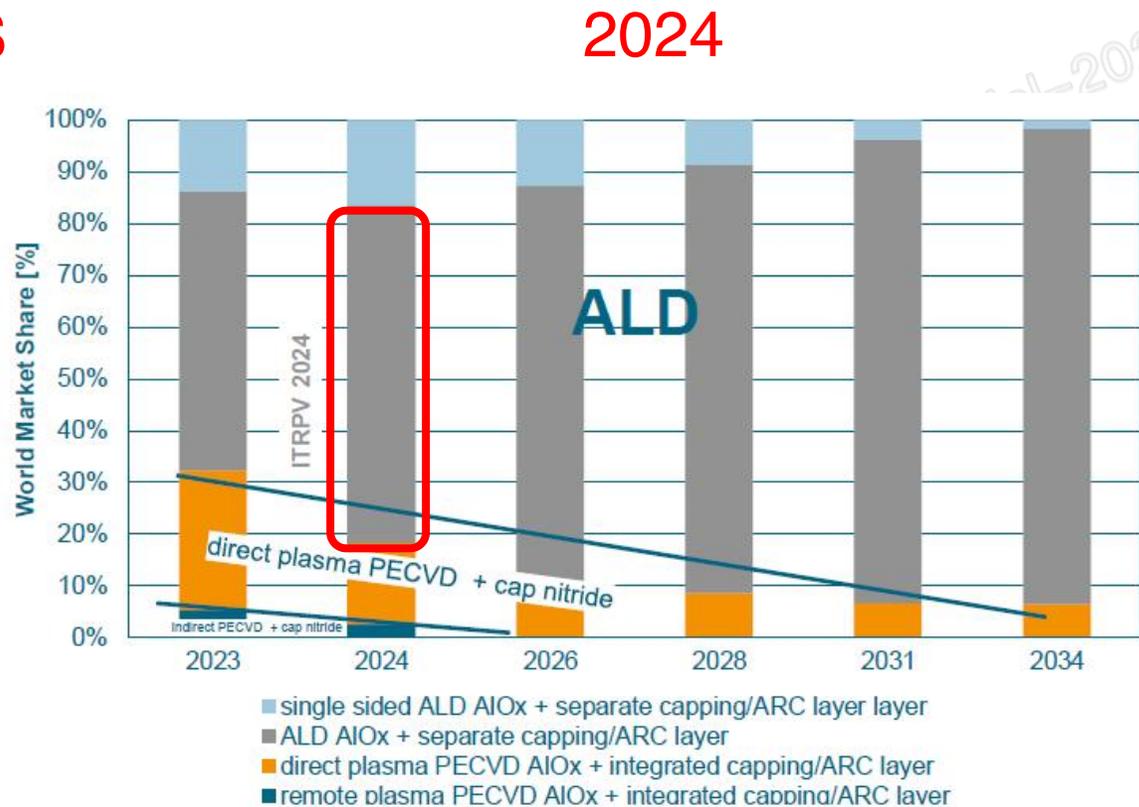
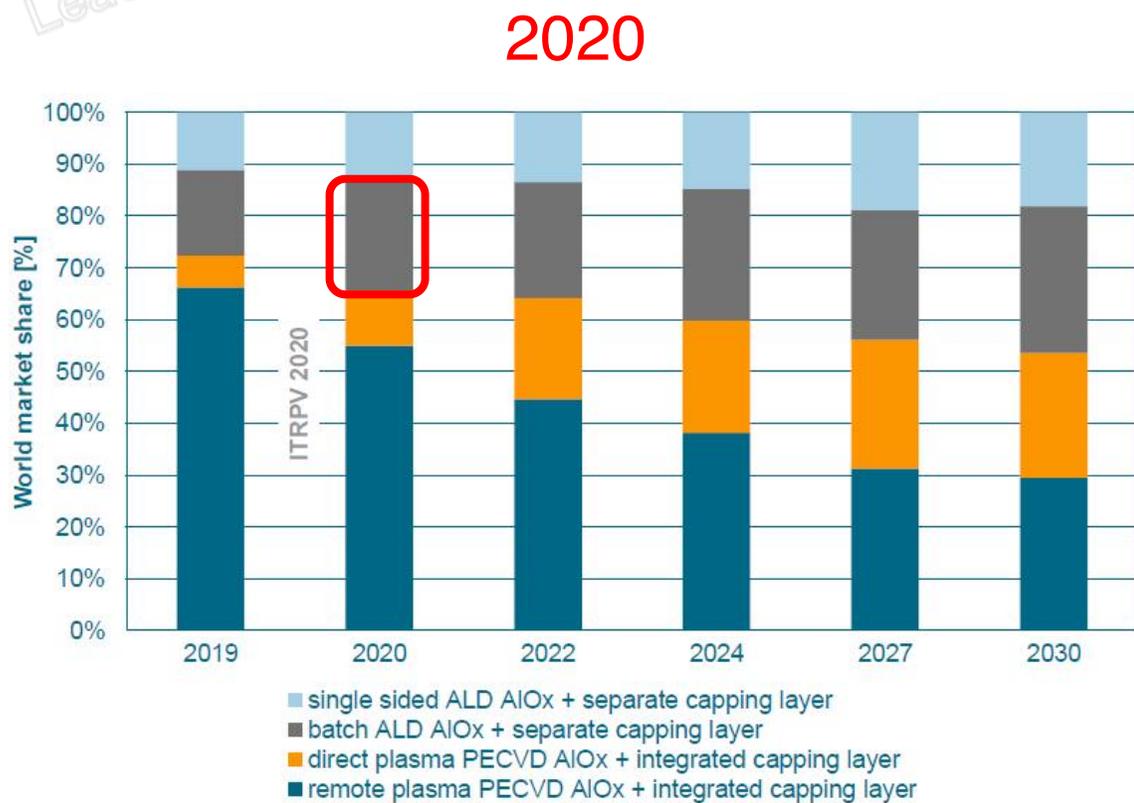
PECVD SiN_x(F&R)

Printing & LAF

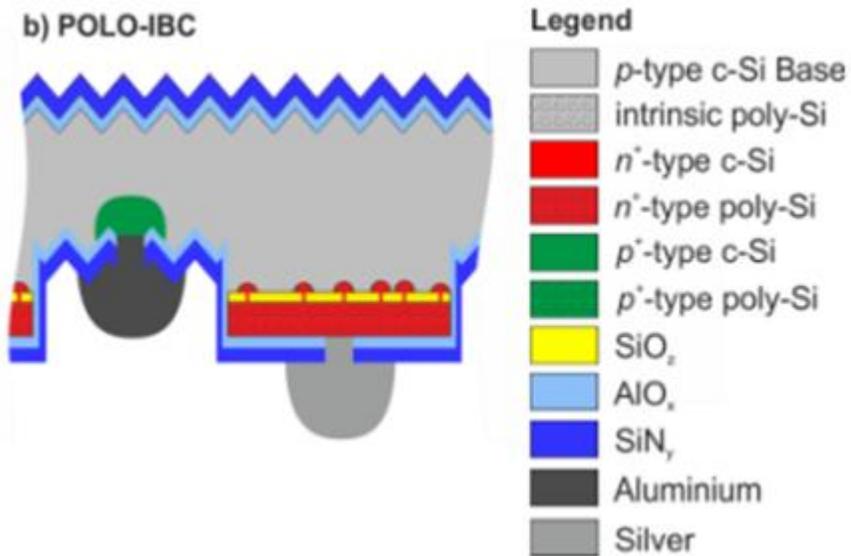
EPD

IV Test

➤ Trend: AlOx deposition PERC/TOPCon/TBC



➤ TBC, HPBC ALD Al_2O_3 New Requirement: double-side coating



Technology	Batch ALD Al_2O_3	In-line ALD	PECVD two-in-one
Efficiency	😊	😊	😞
Equipment Price	😊	😞	😊
Maintenance Period	😊	😞	😐
Operating Costs	😊	😞	😊
Double-side Coating	😊	😞	😞
Wrap-around	😐	😊	😐

Market Share Highest

Capacity Highest

Capacity High

Unique Design



**1.5XBoat Tech.
Capacity 50%↑**

**Each tube work/maint.
independently**

Uptime High

> 98%

Breakage Low

< 0.03%

Maint. Easy

Less powder

COO Low

Highly Automated

High-eff. Cell Tech.

Standard process for TOPCon, XBC, Perovskite, Tandem cells

Compatibility Good

Compatible with various rectangular size wafers

2012:

- Solved the bottlenecks for ALD Al₂O₃ from lab to PERC cell commercialization

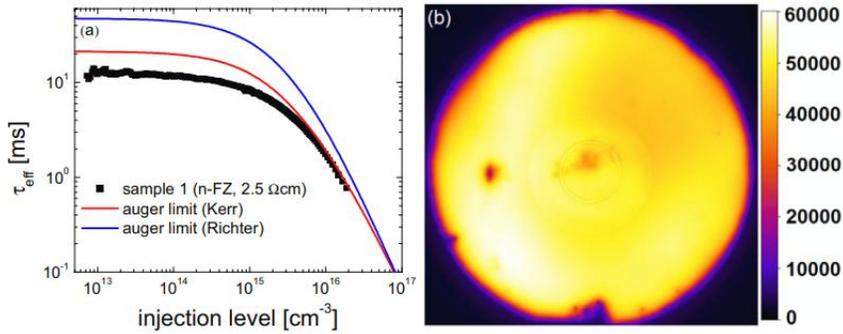


Table 3. A comparison of D_{it} and Q_f for Al₂O₃ under different anneal conditions and deposition methods.

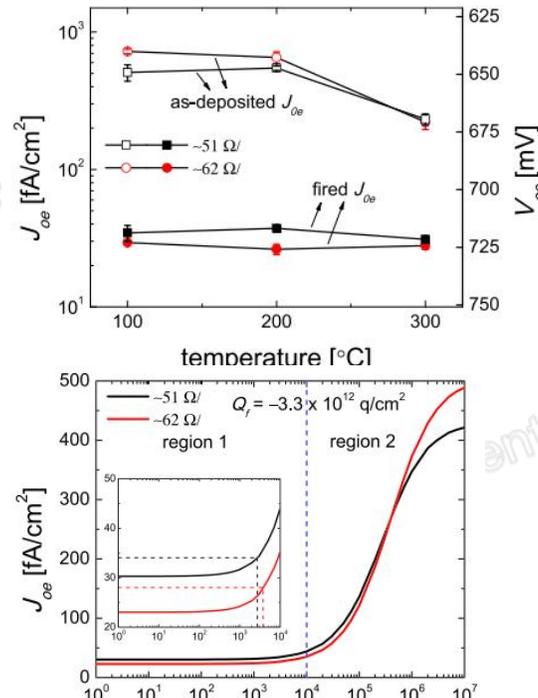
Deposition method	As-deposited		Anneal condition	Annealed/fired		Ref.
	D_{it} (cm ² eV ⁻¹)	Q_f (q/cm ²)		D_{it} (cm ² eV ⁻¹)	Q_f (q/cm ²)	
Plasma ALD	~10 ¹³	(1-3) × 10 ¹²	Annealed 400 °C, N ₂ , 10 min	1 × 10 ¹¹	5.8 × 10 ¹²	[9]
O ₃ -ALD	~10 ¹³	5.3 × 10 ¹²	Annealed 400 °C, N ₂ , 10 min	1 × 10 ¹¹	3.4 × 10 ¹²	[9]
H ₂ O-ALD	3 × 10 ¹¹	1.3 × 10 ¹¹	Annealed 400 °C, N ₂ , 10 min	1 × 10 ¹¹	2.4 × 10 ¹²	[9]
H ₂ O -ALD	3.3 × 10 ¹¹	1.4 × 10 ^{12a} 8.7 × 10 ^{11b}	Fired 800 °C (peak), air, 30 s	0.8 × 10 ^{11a}	3.3 × 10 ^{12a} 3.9 × 10 ^{12b}	This work

^a Obtained by using C-V method.

^b Obtained by using corona charger method.

2013:

- Proved ALD Al₂O₃ excellent surface passivation for boron surface
- Pave the way for today TOPCon's application



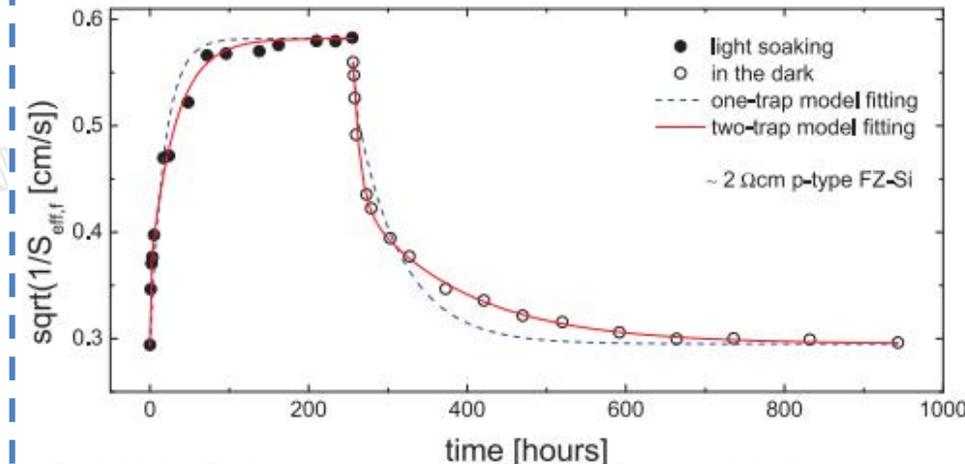
2013:

- Light-soaking mechanisms study

$$\frac{dn_i}{dt} = \frac{n_{0i} - n_i}{\tau_{ti}} - \frac{n_i}{\tau_{di}}$$

$$n_i(t) = \frac{n_{0i}\tau_{di}}{\tau_{ti} + \tau_{di}} \left(1 - \exp\left(-\left(\frac{1}{\tau_{ti}} + \frac{1}{\tau_{di}}\right)t\right) \right)$$

$$\sqrt{\frac{1}{s_{eff}(t)}} = a_0 + \sum_{i=1}^m a_i \left(1 - \exp\left(-\frac{t}{\tau_i}\right) \right)$$



3.1 EPD

PE-TOPCon 4.0

Texture

B Diffusion

SSE

PE Tox/n-Poly

Anneal

Poly-Finger (R)

Poly Clean

ALD AlO_x (F)

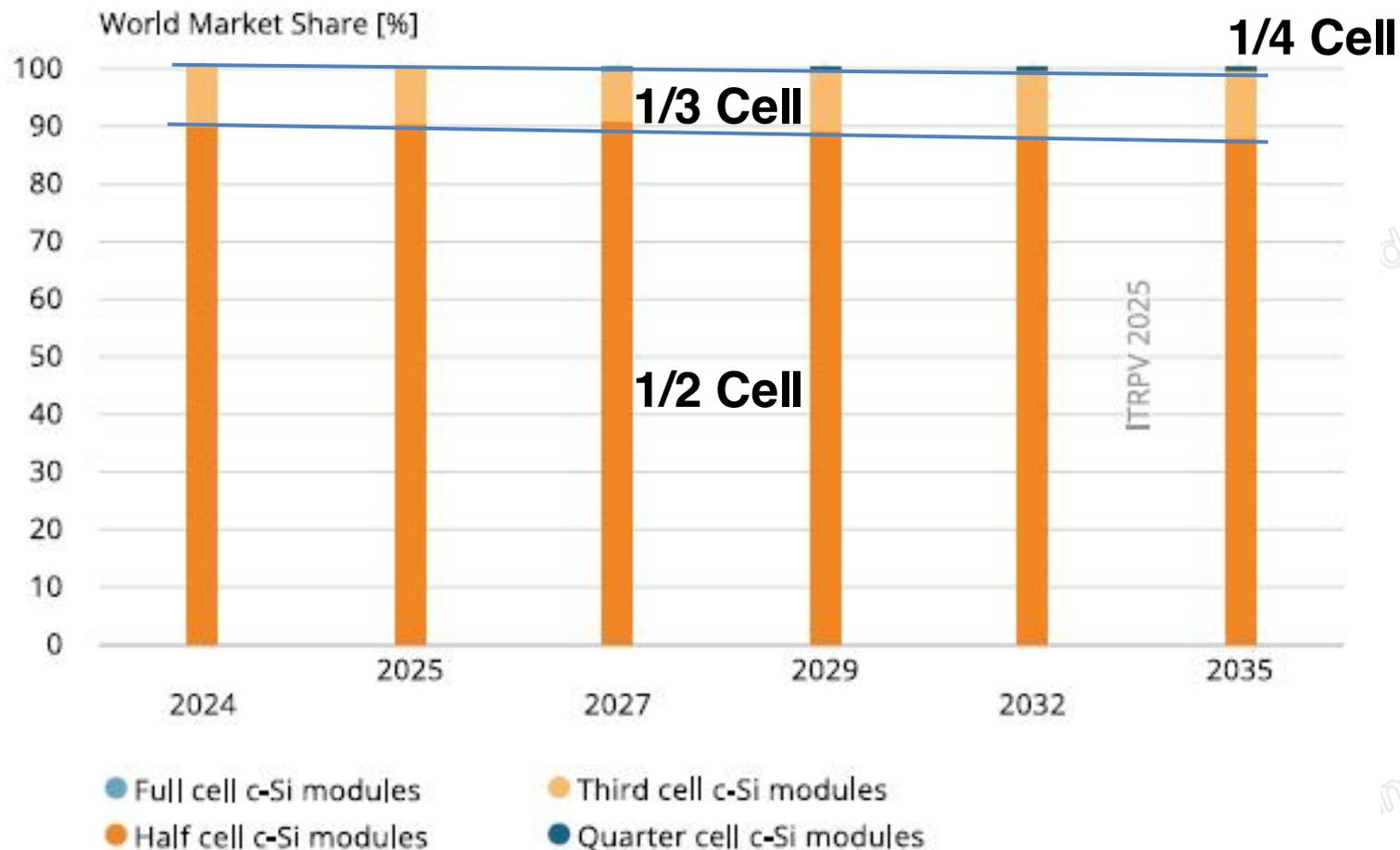
PECVD SiN_x(F&R)

Printing & LAF

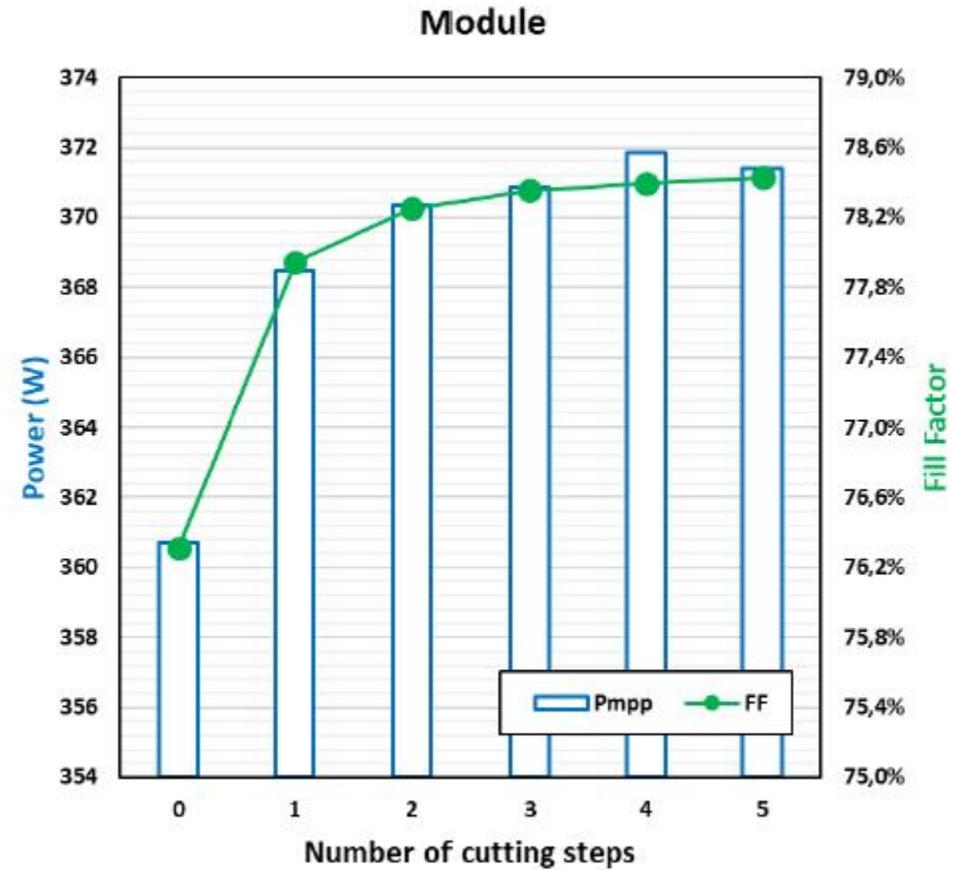
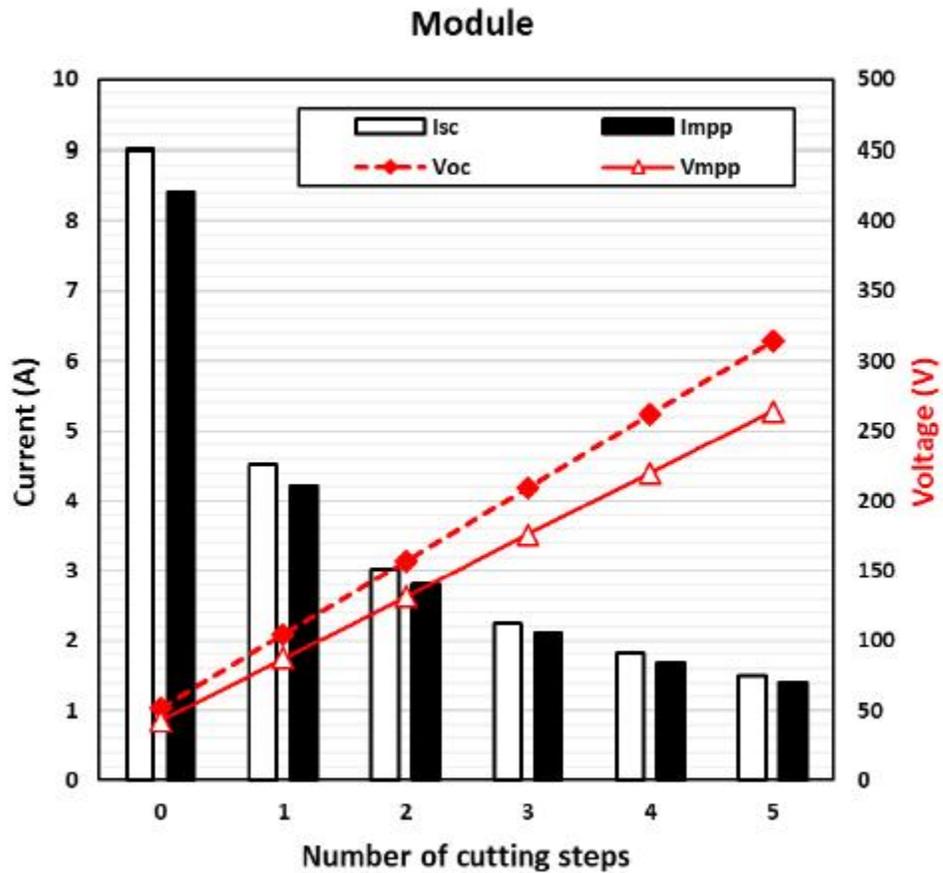
EPD

IV Test

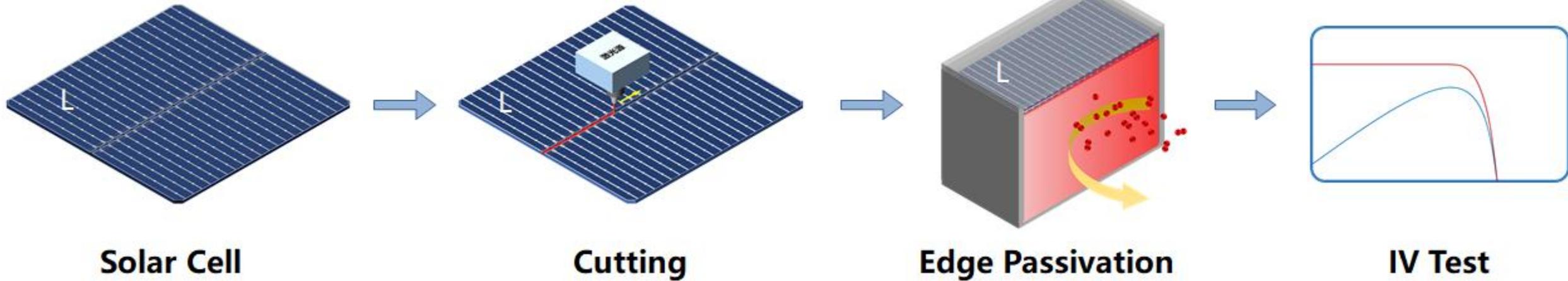
Market Trends (M10 < Wafer Size ≤ G12)



➤ No. of Cuttings: **the more, the better?**



➤ Process flow



Challenges

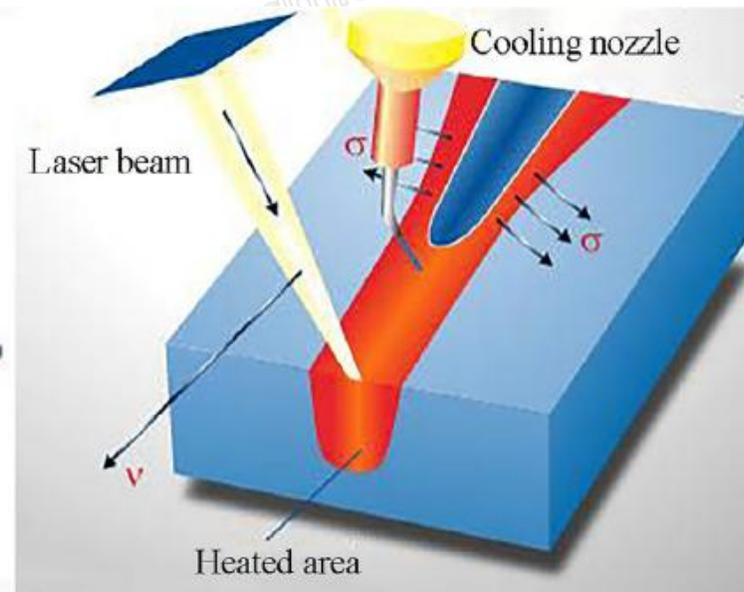
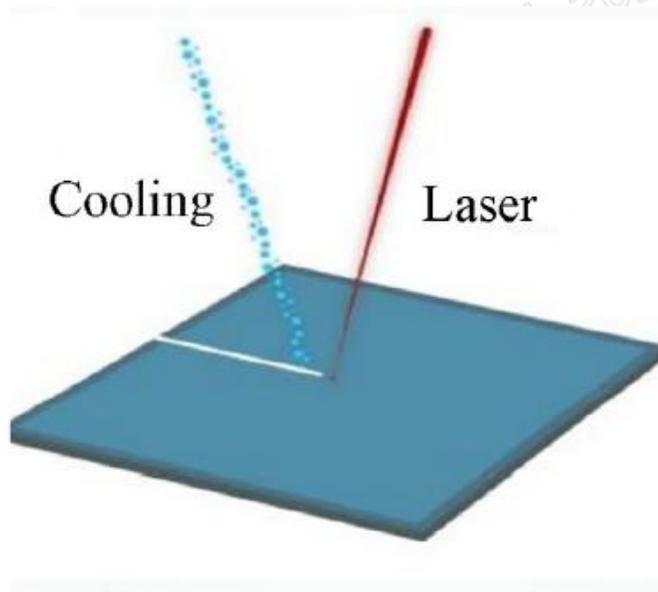
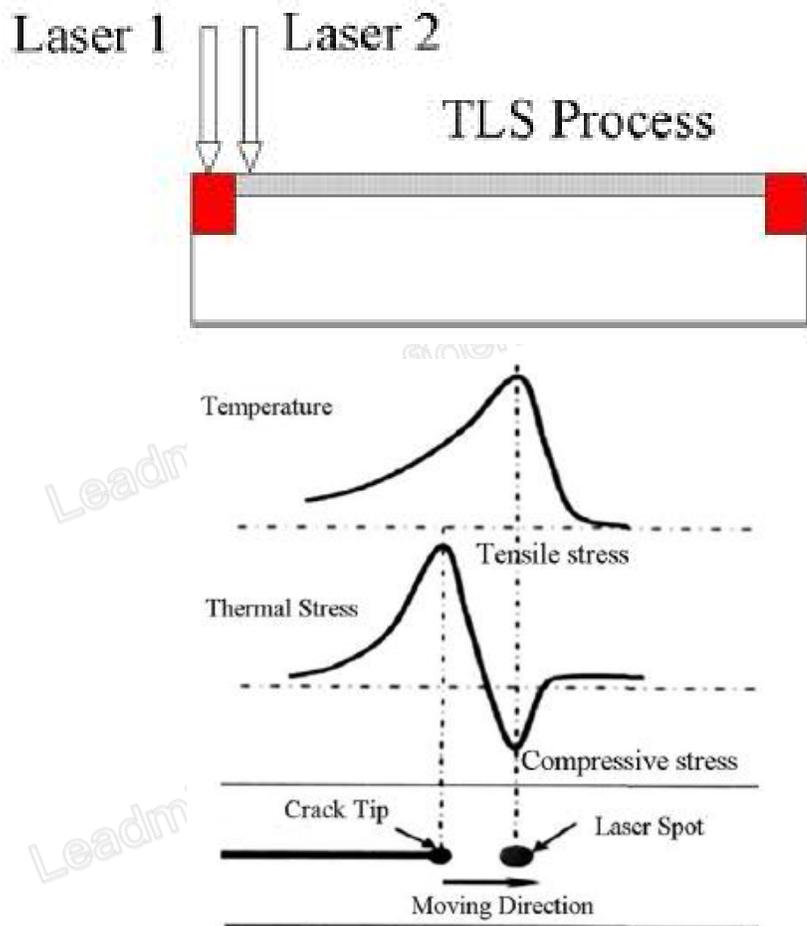
- Damage-free laser cutting ?
- Edge passivation

3.2

Cutting Loss Analysis and Edge passivation Mechanisms

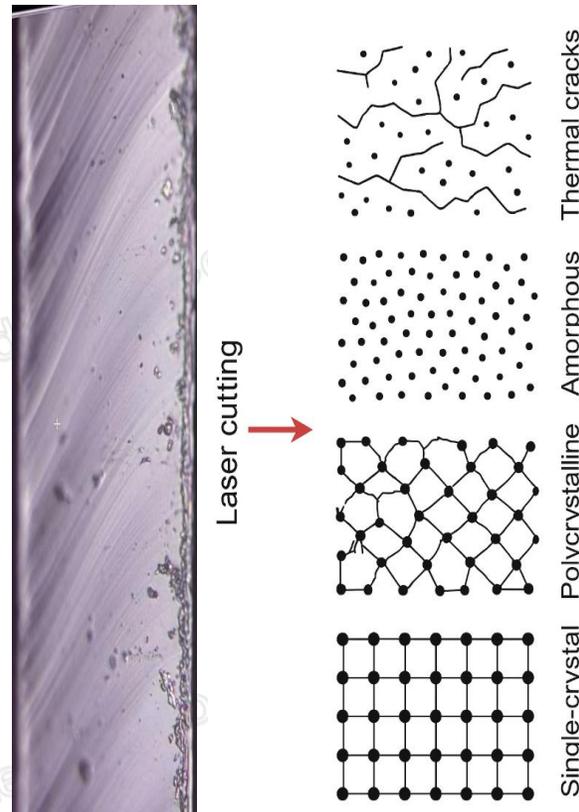
Thermal Laser Separation (TLS) Cutting Technology

➤ Laser Cutting+ "hot" laser sweeping + cooling water → temp. & thermal stress

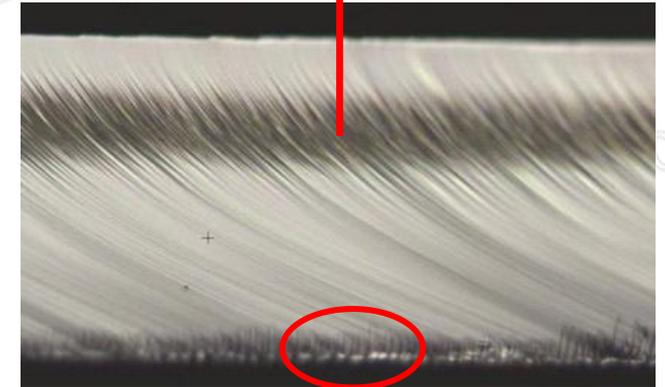


TLS Potential Damages

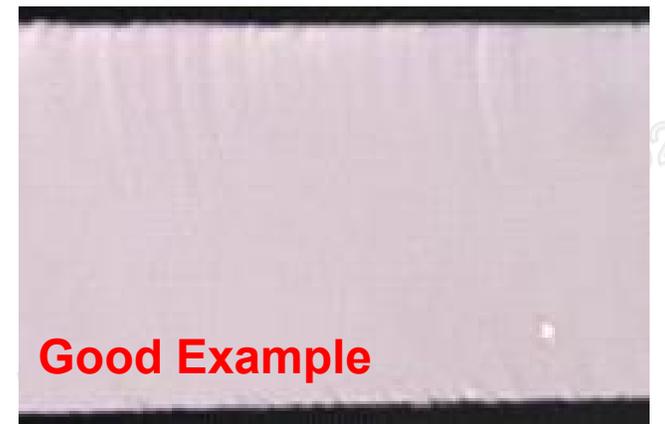
- Thermal damages (e.g. high-temp. melting, thermal cracks)
- Thermal stress (lattice dislocation)
- Dangling bonds
- Debris



uneven break surface
(can be repaired by ALD)

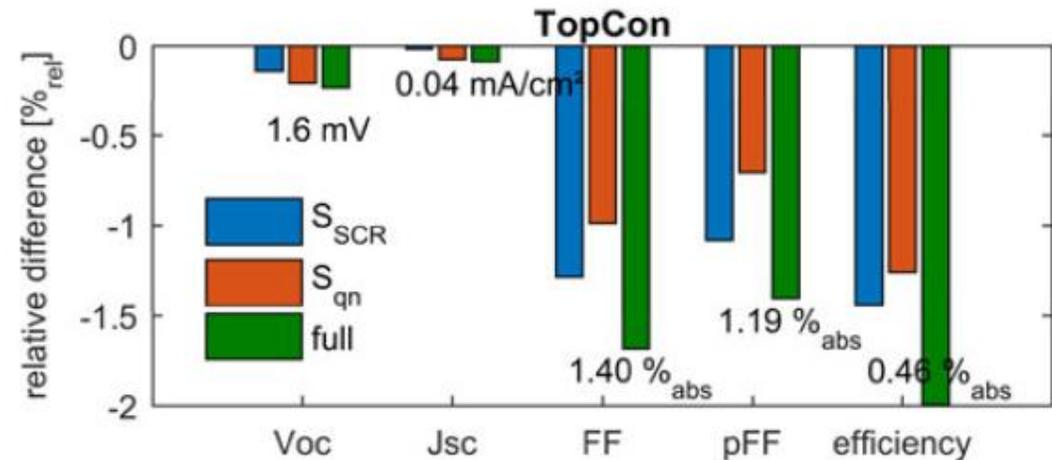
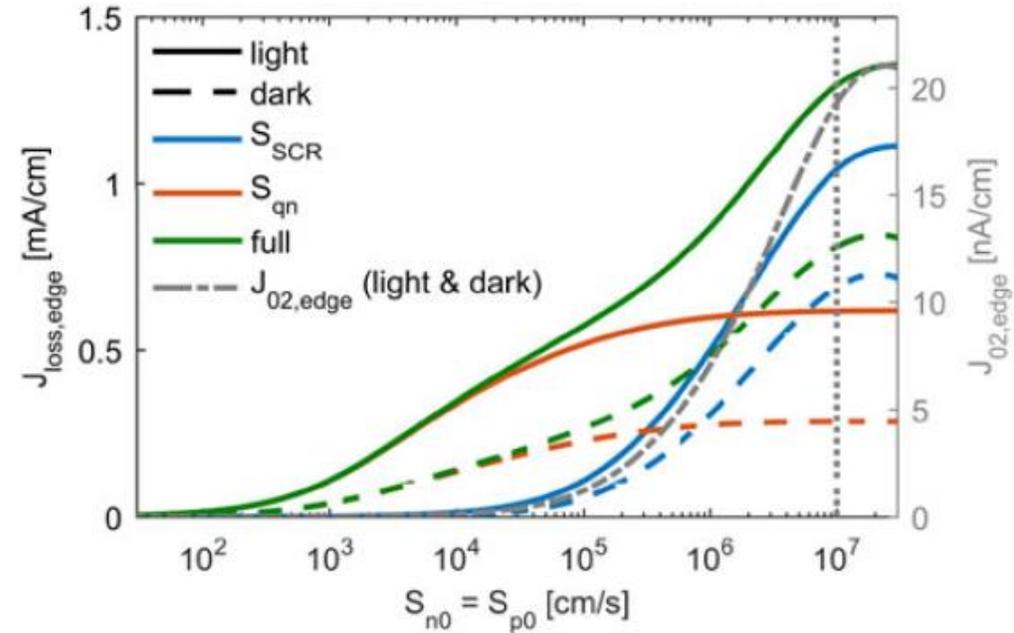
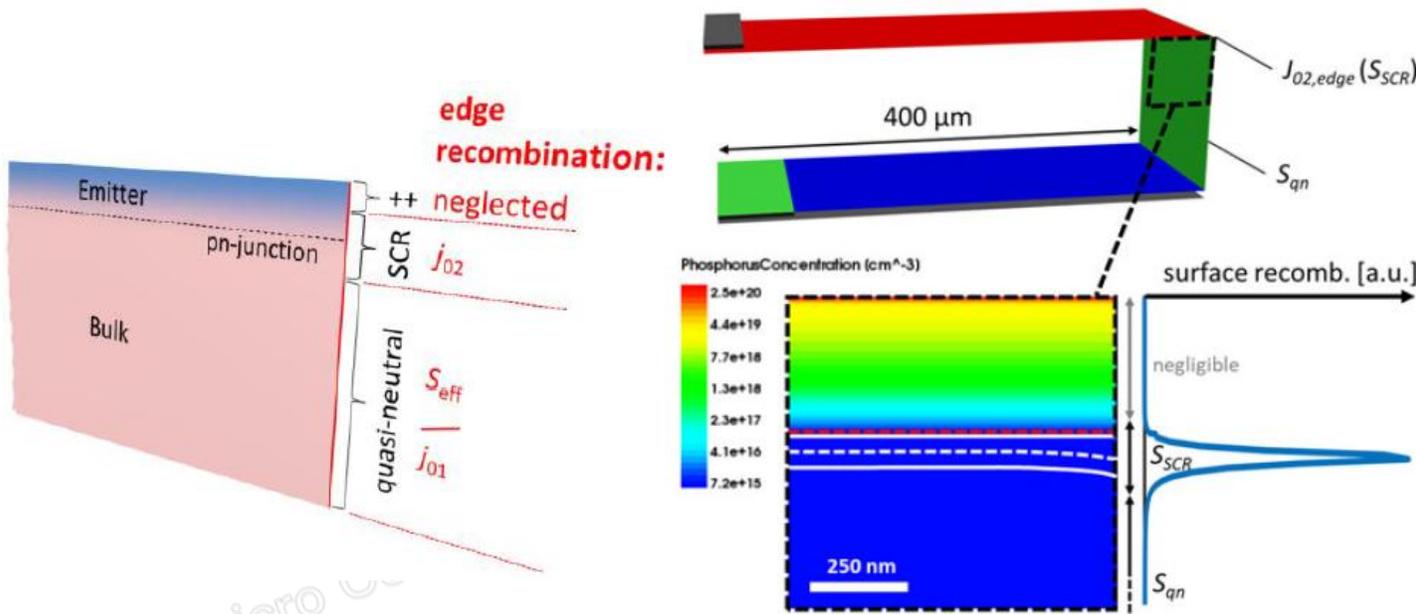


melting (difficult to repair)



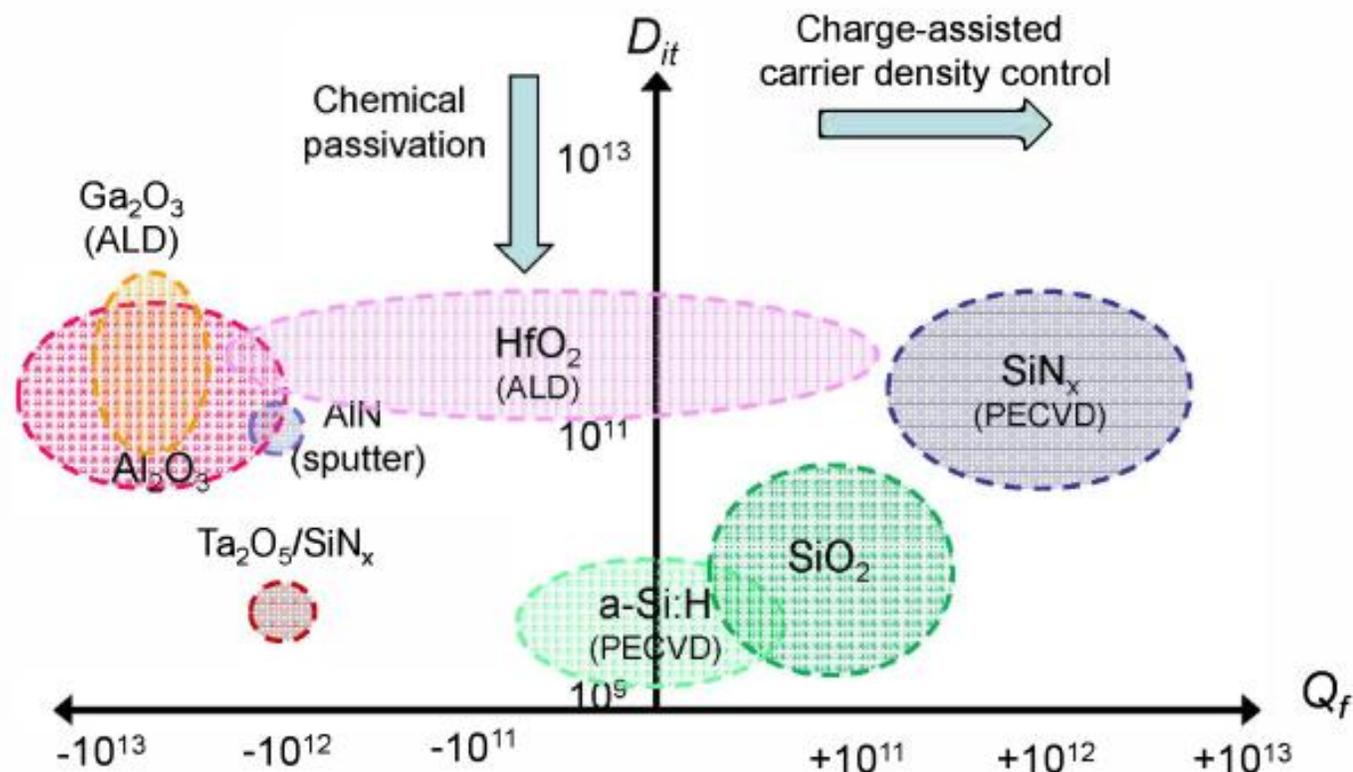
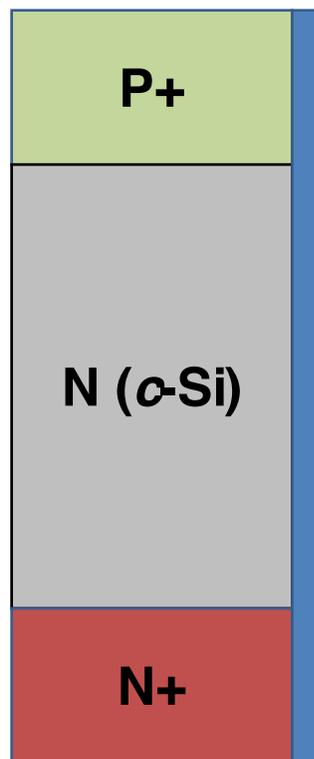
Cutting Loss Analysis (PERC Simulation Data)

- $J_{02,edge}$ dominate , ~ 19 nA/cm ,
- Impact pFF and Voc



Passivation Mechanisms

- Chemical passivation
- Field effect passivation
- H passivation
- Thermal treatment
- Light-soaking treatment



3.3

EPD Equipment Solutions

One-Stop Compatibility

- One-stop compatibility (TOPCon/0BB/Poly Finger/TBC)
- Half, Third, 1/4 Compatible
- M10, G12R , G12
- Cost effective

High Passivation

- Chemical + Field effect + H passivation + thermal + light treatment
- Half > 5 W
- Third > 8 W
- Quarter > 10 W

High Conformality

- Uneven cutting surface (ALD)

High Throughput

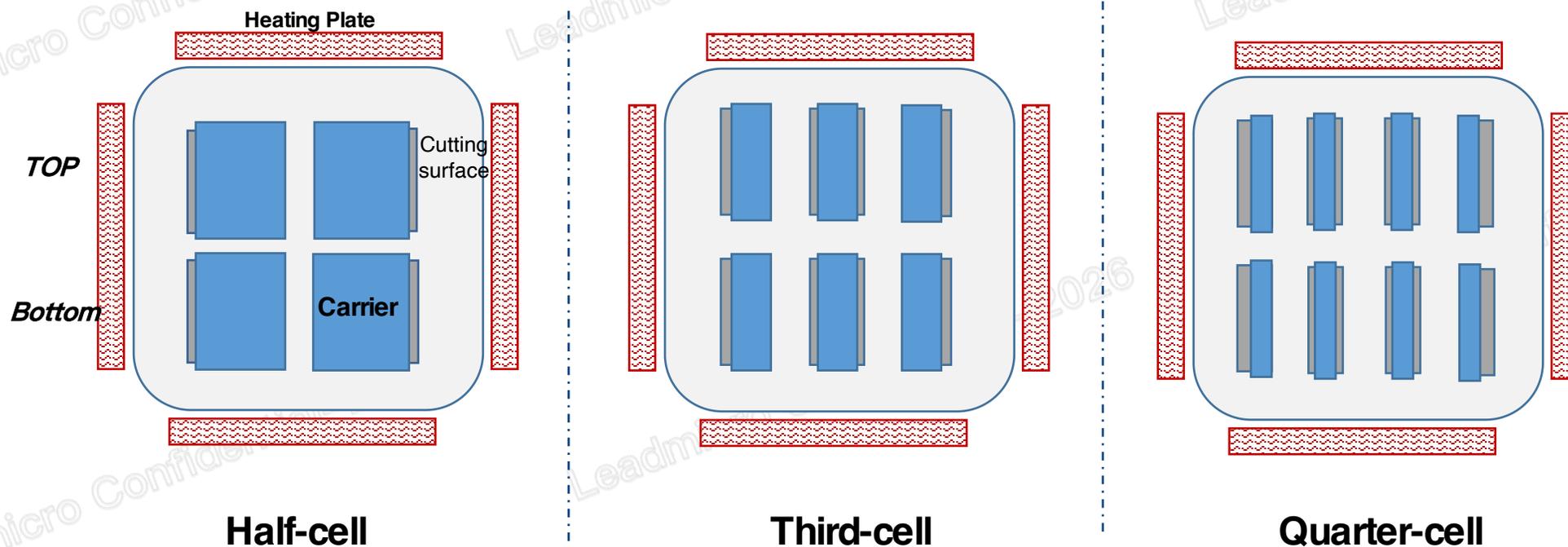
- > 20000 pcs/hr (full cell)

High Stability

- No need frequent maintenance
- Visualized Monitoring
- Mature in Production



Leadmicro Solution: One-Stop Compatibility



- **One-Stop compatibility: TOPCon/0BB/Poly Finger/TBC**
- **Half, Third, 1/4 Compatible: by changing carriers**
- **M10, G12R , G12 Compatible**

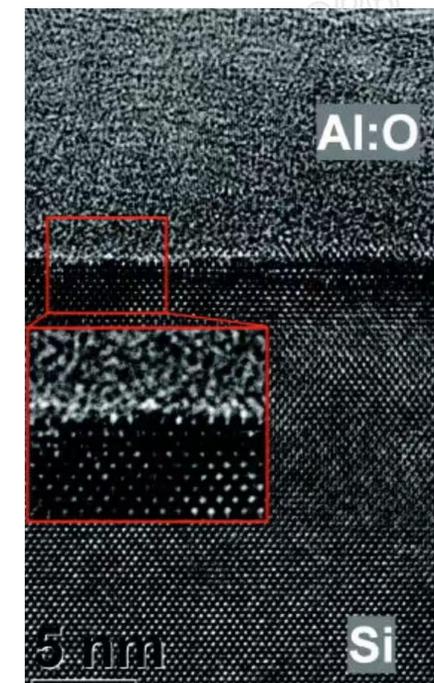
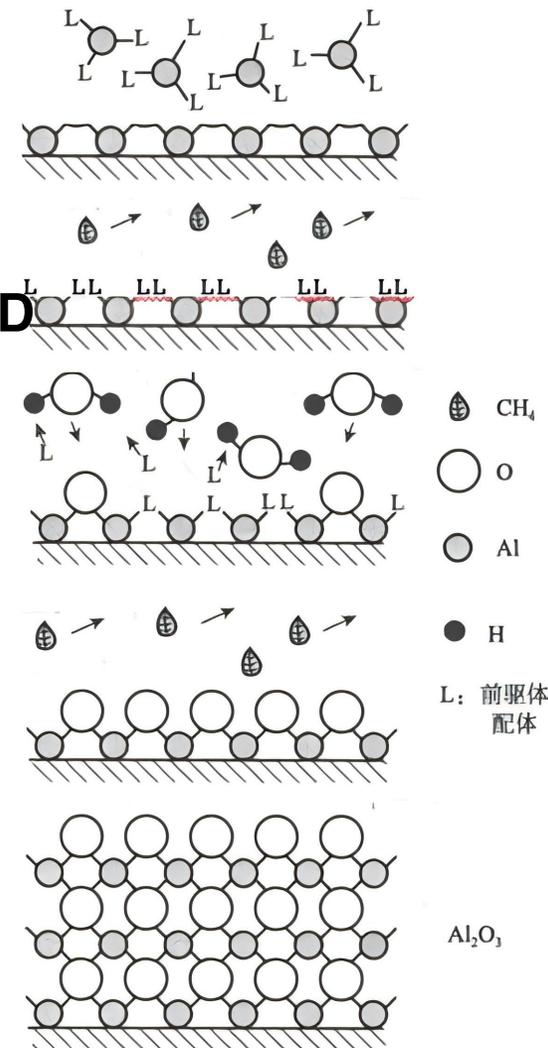
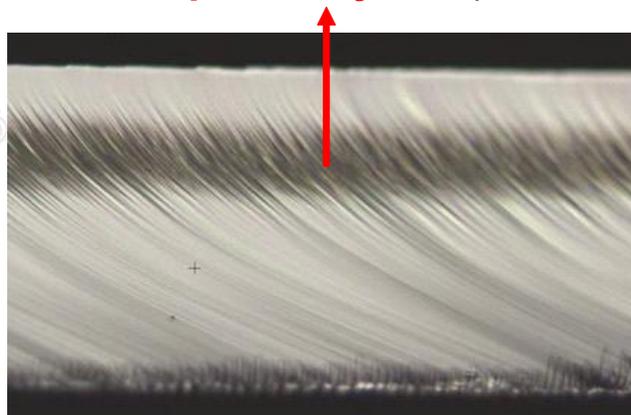
Leadmicro Solutions: **Chemical + Field-effect + H Passivation + Thermal + Light treatments**

- **Tube ALD: High film density → Good D_{it}**
- **AlO_x : High neg. Q_f → Good Field-effect, esp. P+layer**
- **Interface Treatment: “step1-OH pretreatment”+“step2-ALD**

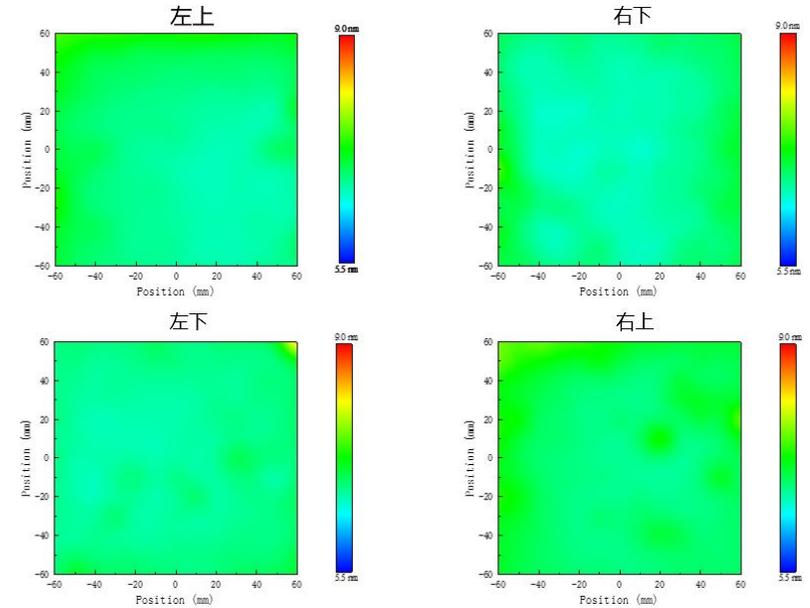
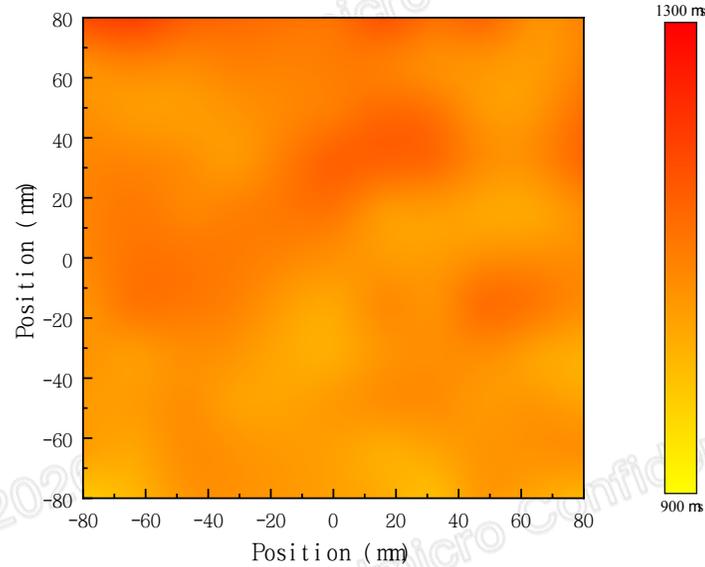
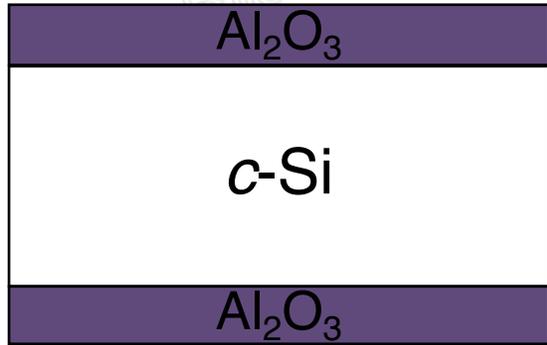
Al_2O_3 ” → **Eta ~0.03%↑**

- **High conformality → Excellent for uneven surface**
- **Half-cell > 5 W**
- **Third-cell > 8 W**
- **Quarter-cell > 10 W**

uneven break surface (can be repaired by ALD)



Film Thickness and Passivation Monitoring



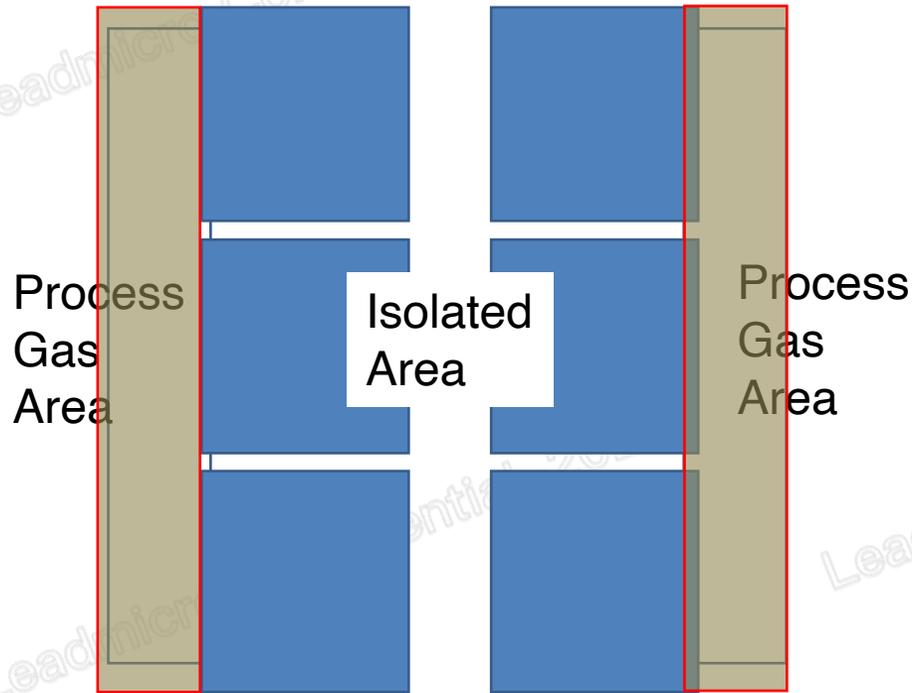
■ Monitoring Sample

■ Passivation Uniformity

■ Thickness Uniformity

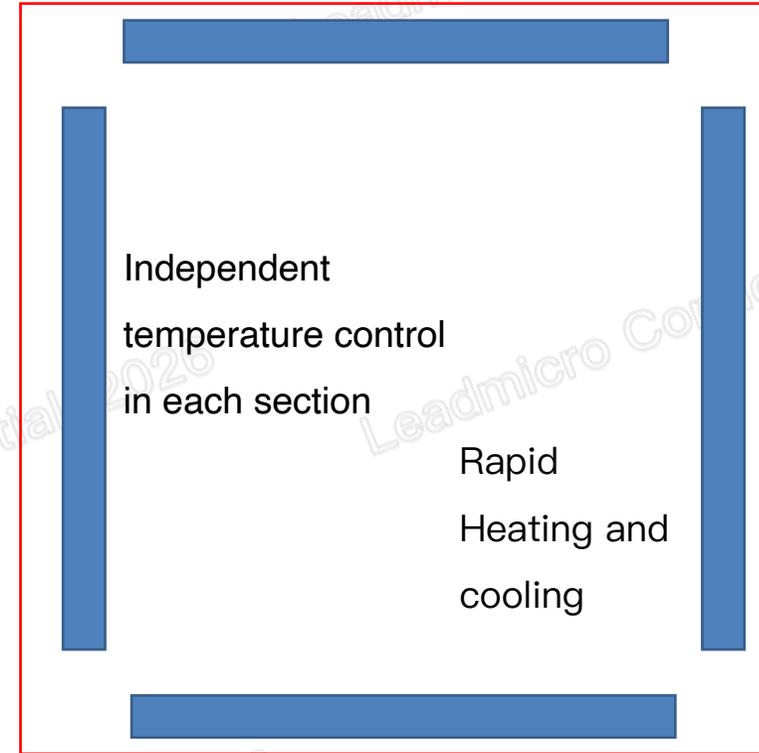
- **Live Visualized Monitoring**: monitor equipment/process stability while production
- Passivation Avg. Lifetime > 760μs;
- Film thickness: WIW < 3%, WTW < 3%;

Equipment Features: Tailored Temp. and Gas Flow Design



Completely New Gas Flow System Design

- **Low chemical consumption**
- Individual gas line control system



Unique Temp. Field Design and Control System

- **Better passivation performance**
- **Avoid wafer stick issue**

3.4

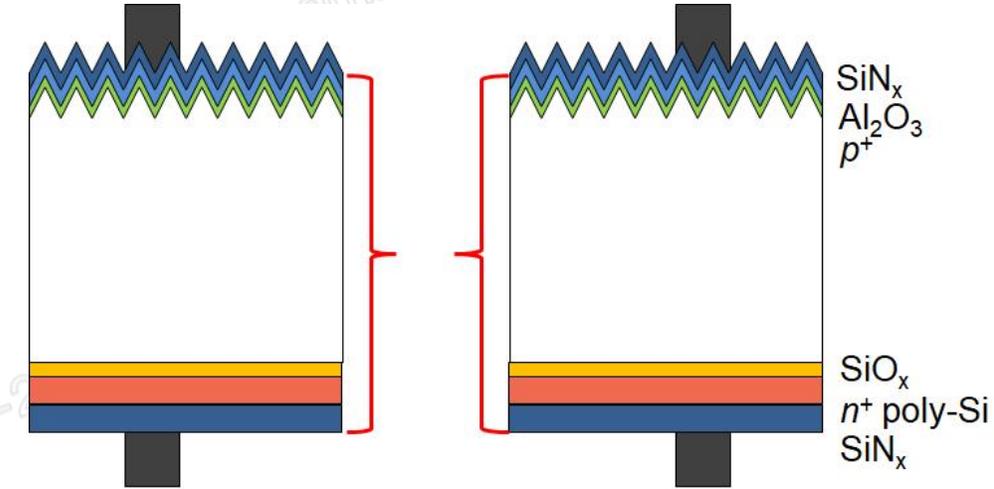
Future Outlook

Leadmicro AEPD 1.0 Tech.

TMA +
H₂O

Wrap-around

< 3mm

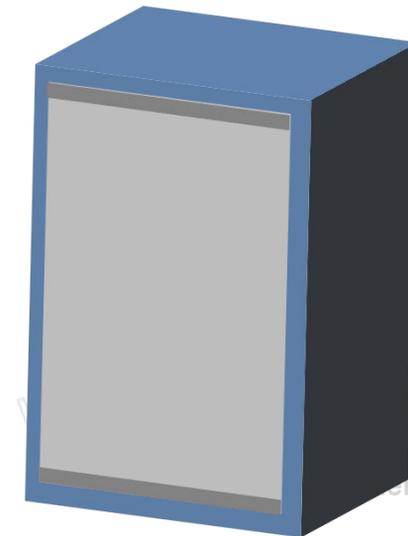


Leadmicro AEPD 2.0 New Tech.

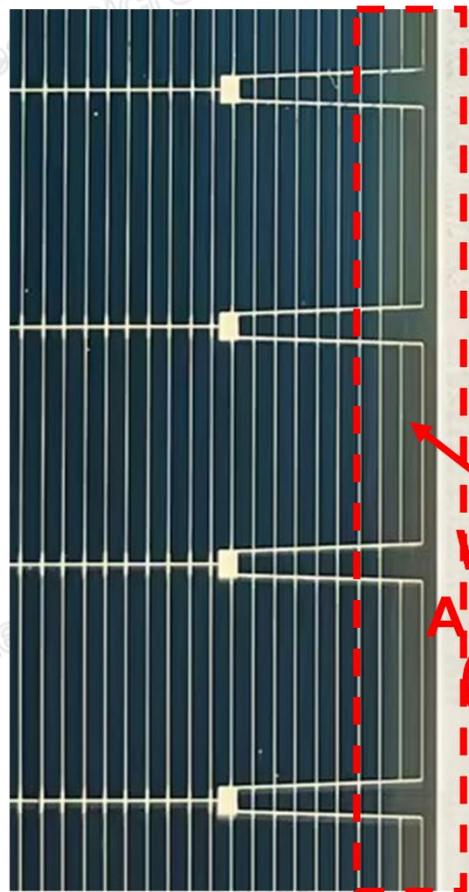
TMA +
O₃

Wrap-around

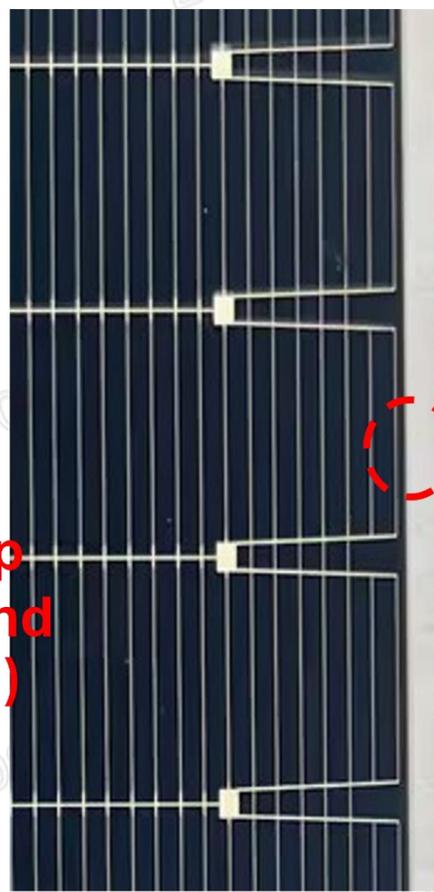
< 0.01mm



EPT 1.0 Tech.



EPT 2.0 New Tech.



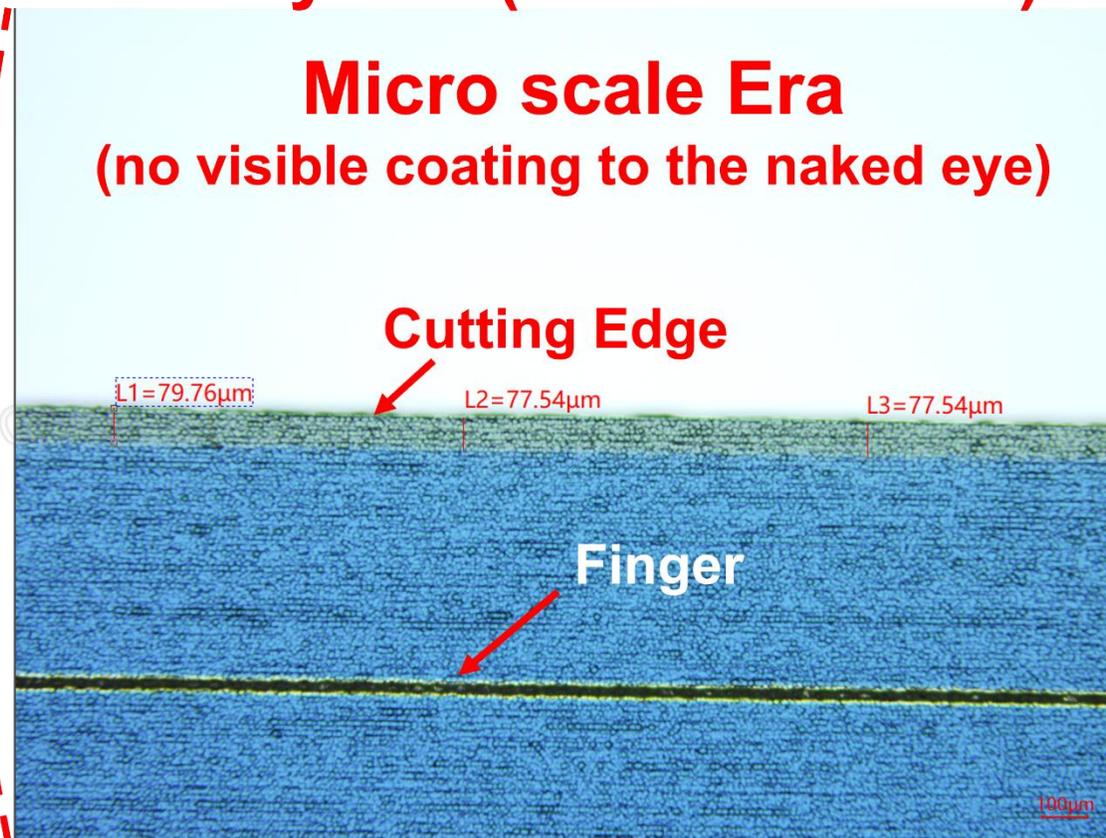
Wrap Around (WA)

WA > 3 finger lines
Visible

WA << 1 finger line
Not Visible

400 cycles (WA < 0.01 mm)

Micro scale Era
(no visible coating to the naked eye)



04

Company Introduction

One of the world largest ALD company

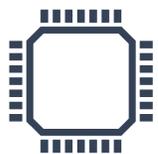
- World 1st IPO company with ALD core technology
- >2000 employee with > 36% R&D staff
- >20% R&D expenditure (> 20M USD in 2023)

No.1 ALD provider for PV industry in the world

- >3000 ALD reactors delivered
- >800 GW capacity cumulatively

No.1 ALD provider in SEMI industry in China

- >100 delivered/to be delivered ALD systems
- >300% rapid growth in 2023
- Only production proven supplier of 300mm ALD tool in China



半导体

Semiconductor



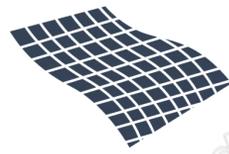
光伏

Photovoltaics



新能源

New Energy



新材料

New Material



产业化应用中心

IAC



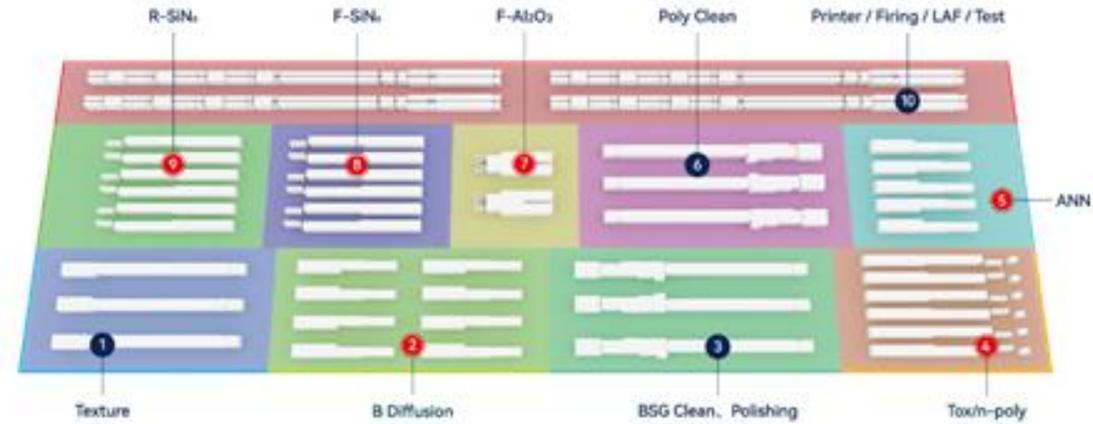
- The intellectual property across China, United States, continental Europe, Japan, Germany , India , South Korea and other countries and regions.
 - Patent Application > 760 ;
 - Granted IP > 230 ;
 - Proprietary Technologies > 3,000 ;
 - Global Registered Trademarks > 110.

The number of patent applications maintains a stable growth, with invention patent applications accounting for more than 60%.

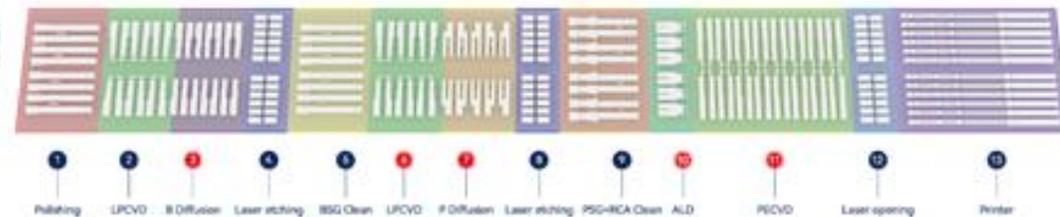
The IP conversion rate exceeds 80%, of which the industrialization rate of the company's effective invention patents exceeds 76%



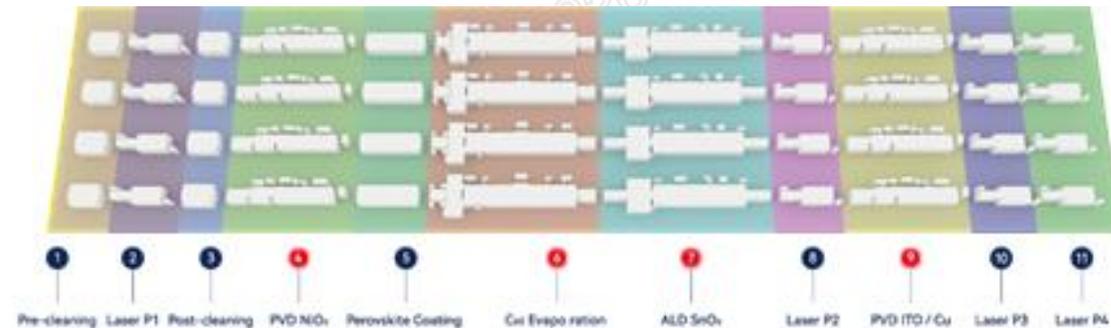
PE-TOPCon 4.0 Turnkey Solution



TBC Turnkey Solution



Perovskite/Tandem Turnkey Solution



KF	ZR	XH	JW	Laser	HY
KF20000S	ZR6000	XH10000	EPD40000		HY10000
					
Batch ALD/CVD	PECVD/PEALD	Diffusion Anneal Oxidation LPCVD	Edge Passivation	SE LAF Poly Thinning TBC Patterning Laser Cutting	In-line ALD/PEALD /PECVD
Al ₂ O ₃ , SiO ₂ , TiO ₂ , SnO _x , TCO	Al ₂ O ₃ , SiN _x , SiO ₂ , poly-Si (n&p), a-Si	O ₂ , BBr ₃ , BCl ₃ , POCl ₃ , poly-Si	Al ₂ O ₃		Al ₂ O ₃ , SiN _x , SiO ₂ , poly-Si (n&p), a-Si

HY	iSparol	SuiR MS	SuiR EVA	Laser
				
<p>In-line ALD/PEALD /PECVD</p>	<p>RTR Platform ALD</p>	<p>Magnetron Sputtering</p>	<p>Evaporation</p>	<p>P1-P4</p>
<p>Al_2O_3, SiN_x, SiO_2, poly-Si (n&p), a-Si</p>	<p>Al_2O_3, SiO_2, TiO_2, SnO_x</p>	<p>NiO_x, ITO, Cu/Ag</p>	<p>LiF, C60</p>	

Global Market Leader in ALD technology for PV industry

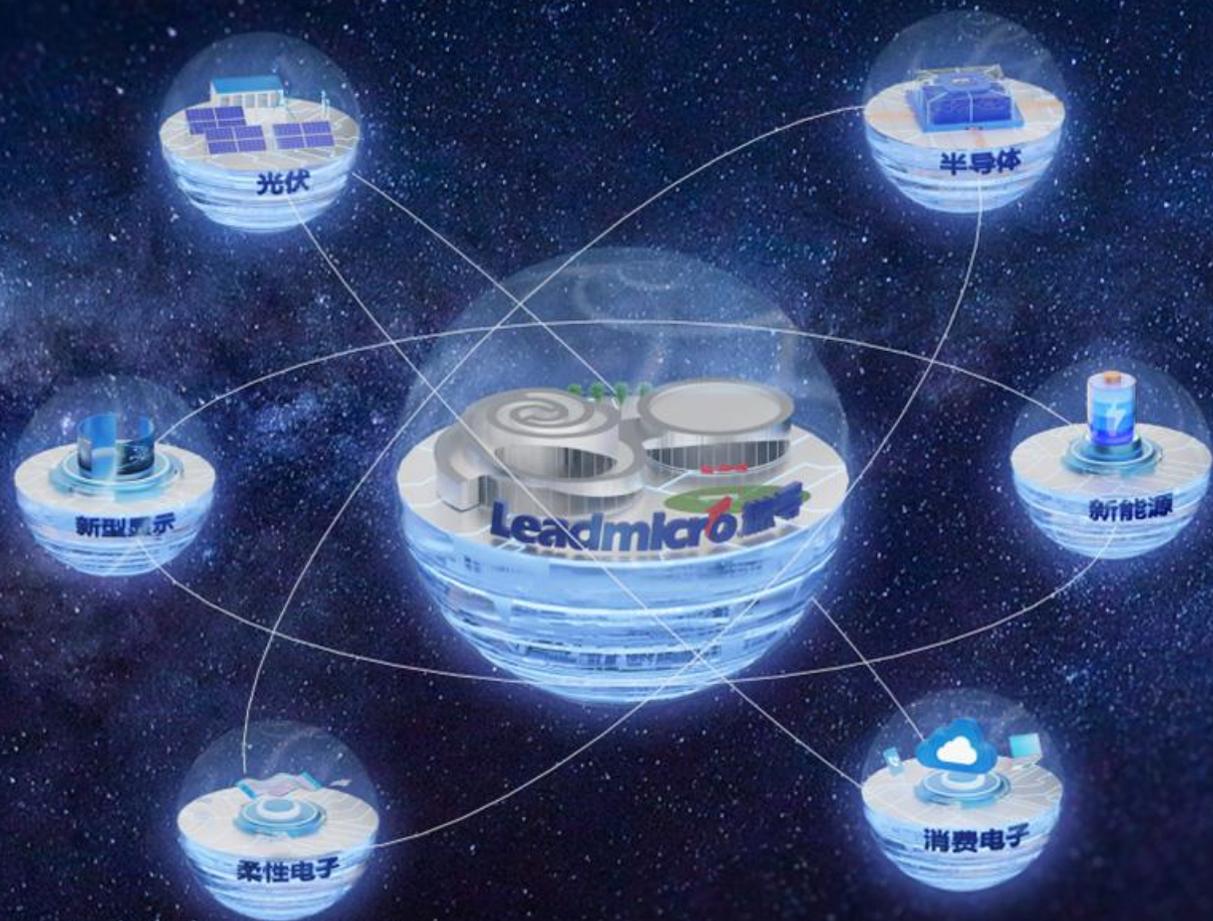


900GW+ ALD Equipment Delivered

200GW+ PECVD-ToxPoly Equipment Delivered

20 GW+ PE-TOPCon Turnkey Project Delivered

- Recent Progress of Cell Technologies
- TOPCon 4.0 Equipment Solutions
 - ✓ Rear Poly Finger: Laser Solution
 - ✓ ALD: 1.5X Boat Tech., capacity improved \approx 50%
 - ✓ EPD: Half Cell in production > 5W
 - Cutting Loss Analysis and Edge passivation Mechanisms
 - Leadmicro EPD Equipment Solutions
 - Excellent Compatibility: TOPCon/Poly Finger/TBC, Half, Third, 1/4 Cells, M10, G12R, G12
 - Excellent Passivation: Chemical + Field effect + H + thermal + light treatment
 - High Throughput (> 20000 pcs/hr)+Conformality (uneven surf.)+Stability (Live monitoring)
 - EPD Future Outlook: nil wrap-around technology, 1/3, 1/4 cell technology



谢谢
THANK YOU